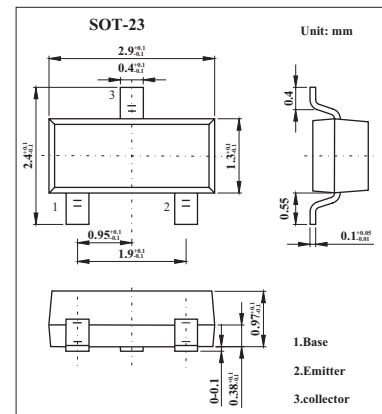


Silicon NPN Epitaxial

2SC3326

■ Features

- High emitter-base voltage: $V_{EBO} = 25 \text{ V (min)}$.
- High reverse h_{FE} : Reverse $h_{FE} = 150 \text{ (typ.)}$ ($V_{CE} = -2 \text{ V}$, $I_C = -4 \text{ mA}$).
- Low on resistance: $R_{ON} = 1 \ \Omega \text{ (typ.)}$ ($I_B = 5 \text{ mA}$).
- High DC current gain: $h_{FE} = 200 \sim 1200$.
- Small package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	25	V
Collector current	I_C	300	mA
Base current	I_B	60	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +125	$^\circ\text{C}$

2SC3326

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Collector cut-off current	ICBO	V _{CB} = 50 V, I _E = 0			0.1	μA	
Emitter cut-off current	IEBO	V _{EB} = 25 V, I _C = 0			0.1	μA	
DC current gain	hFE	V _{CE} = 2 V, I _C = 4 mA	200		1200		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 30 mA, I _B = 3 mA		0.042	0.1	V	
Base-emitter voltage	V _{BE}	V _{CE} = 2 V, I _C = 4 mA		0.61		V	
Transition frequency	f _T	V _{CE} = 6 V, I _C = 4 mA		30		MHz	
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		4.8	7	pF	
Switchingtime Turn-on time	t _{on}	<p>Duty cycle ≤ 2%</p>		160		ns	
Storage time	t _{stg}				500		ns
Fall time	t _f				130		ns

■ hFE Classification

Marking	CC	
	A	B
hFE	200~700	350~120